

P-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Advanced trench cell design
- Low Thermal Resistance

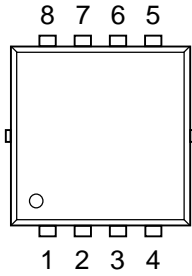
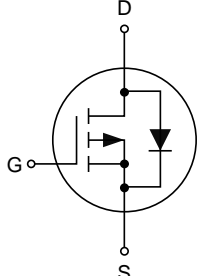
1.2 Applications

- Motor drivers
- DC/DC Converter

1.3 Quick reference

- $BV \geq -30V$
- $R_{DS(ON)} \leq 8.8m\Omega @ V_{GS} = -10V$
- $P_{tot} \leq 20W$
- $R_{DS(ON)} \leq 13m\Omega @ V_{GS} = -4.5V$
- $I_D \leq -40A$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source(S)	 <p style="text-align: center;">Top View PDFN3.3x3.3-8L</p>	
4	Gate(G)		
5,6,7,8	Drain(D)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}C$	-30	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}C$	-	± 20	V
I_D^*	Drain Current	$T_C=25^{\circ}C, V_{GS}=-10V$	-	-40	A
$I_{DM}^{*,**,***}$	Pulsed Source Current	$T_C=25^{\circ}C, V_{GS}=-10V$	-	-144	A
P_{tot}^*	Total Power Dissipation	$T_C=25^{\circ}C$	-	20	W
T_{stg}	Storage Temperature		-55	150	$^{\circ}C$
T_J	Junction Temperature		-	150	$^{\circ}C$
I_S	Diode Forward Current	$T_C=25^{\circ}C$	-	-40	A
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	6	$^{\circ}C/W$

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10$ sec
- ** Pulse width $\leq 10\mu s$, duty cycle $\leq 1\%$
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ30P03Q	<div style="display: inline-block; border: 1px solid black; padding: 2px;"> 30P03Q YWWXXX </div> YWW: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ30P03Q	PDFN3.3x3.3-8L			5000	

Note: KUAIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_C = 25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.0	-	-2.0	V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C	-	-	-30	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A	-	7.8	8.8	mΩ
		V _{GS} =-4.5V, I _D =-10A	-	11.8	13	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-20A, V _{GS} =0V	-	-	-1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =-20A, dI _{SD} /dt=100A/μs	-	21	-	ns
Q _{rr}	Reverse Recovery Charge		-	14	-	nC
Dynamic Characteristics^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V Frequency=1MHz	-	3651	-	pF
C _{oss}	Output Capacitance		-	341	-	
C _{rss}	Reverse Transfer Capacitance		-	278	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =-15V, V _{GEN} =-10V, R _G =4.5Ω, R _L =0.75Ω, I _D =-20A	-	42.8	-	ns
t _r	Turn-on Rise Time		-	89	-	
t _{d(off)}	Turn-off Delay Time		-	409	-	
t _f	Turn-off Fall Time		-	193	-	
Gate Charge Characteristics^b						
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _{DS} =-20A	-	59	-	nC
Q _{gs}	Gate-Source Charge		-	13	-	
Q _{gd}	Gate-Drain Charge		-	7.7	-	

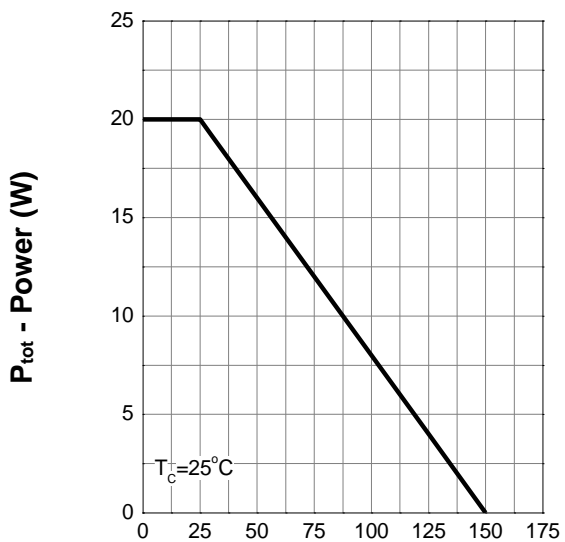
Notes:

a: Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%

b: Guaranteed by design, not subject to production testing

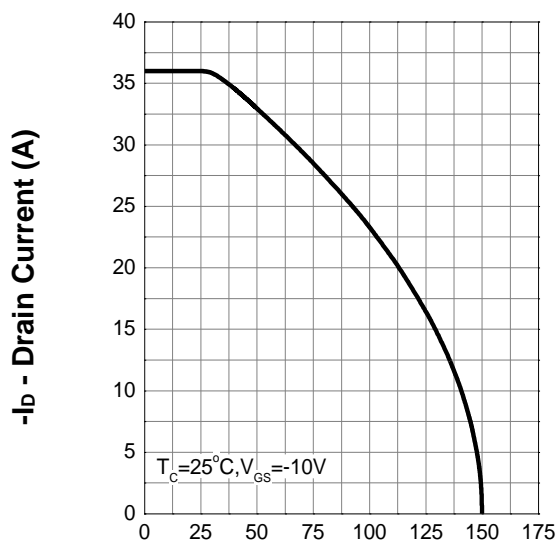
7. Typical Characteristics

Power Capability



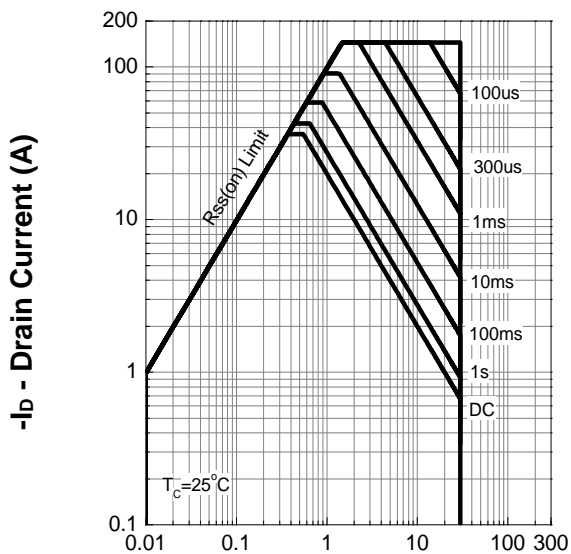
T_j - Junction Temperature (°C)

Current Capability



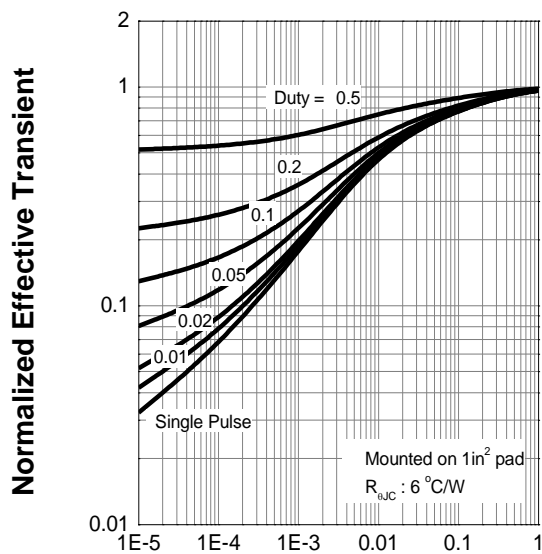
T_j - Junction Temperature (°C)

Safe Operation Area



-V_{DS} - Drain-Source Voltage (V)

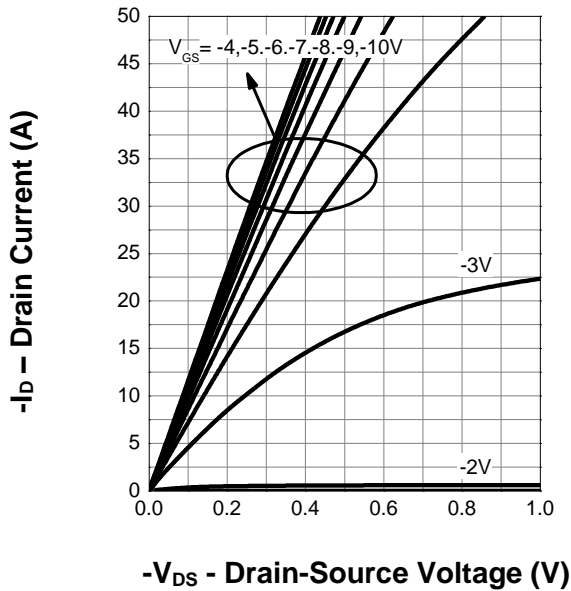
Thermal Transient Impedance



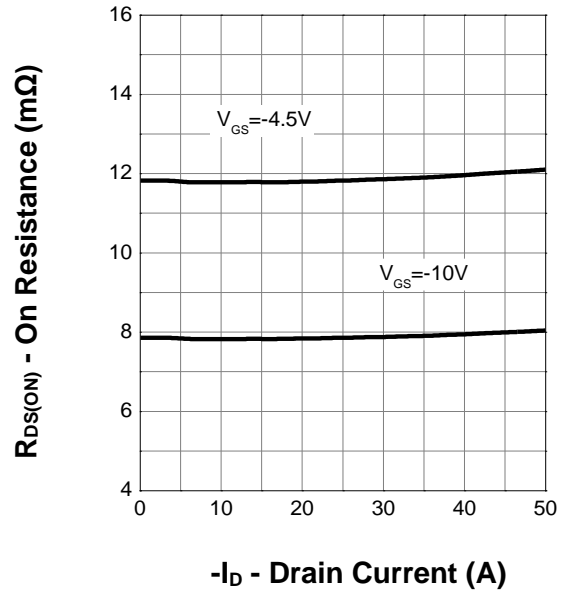
Square Wave Pulse Duration (sec)

7. Typical Characteristics (cont.)

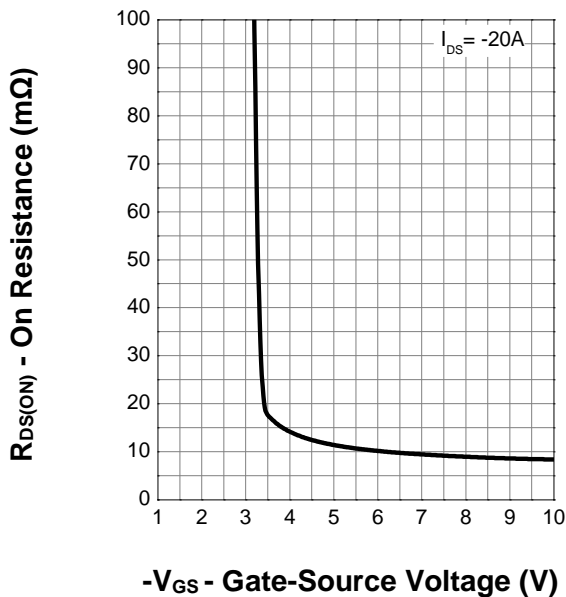
Output Characteristics



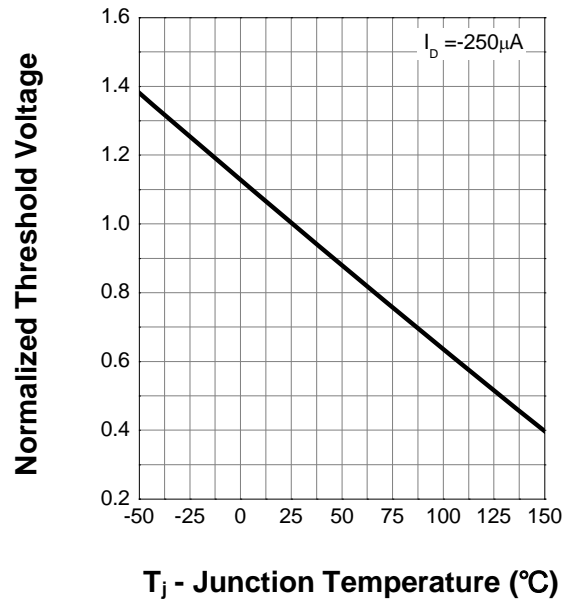
Drain-Source On Resistance



Transfer Characteristics

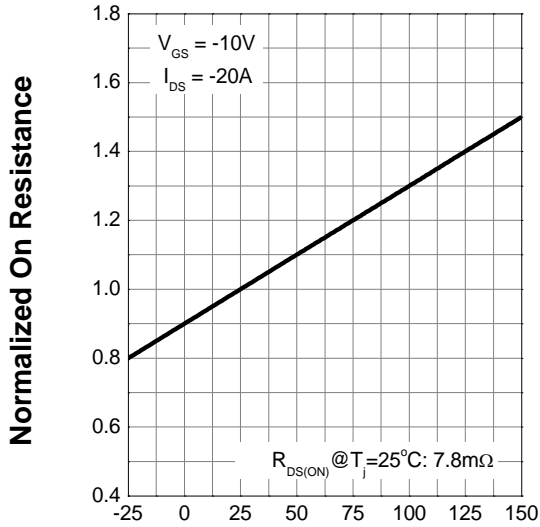


Gate Threshold Voltage



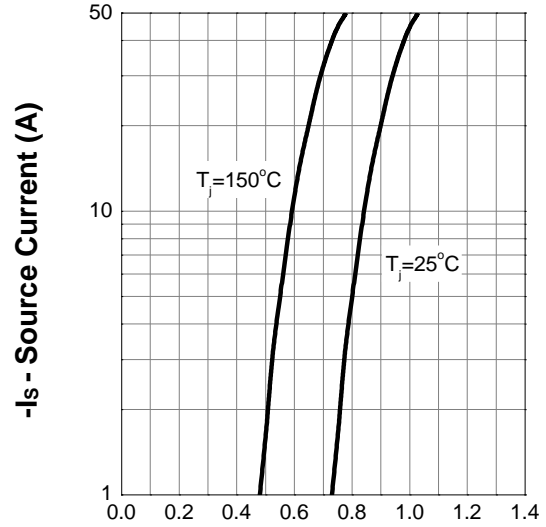
7. Typical Characteristics (cont.)

Drain-Source On Resistance



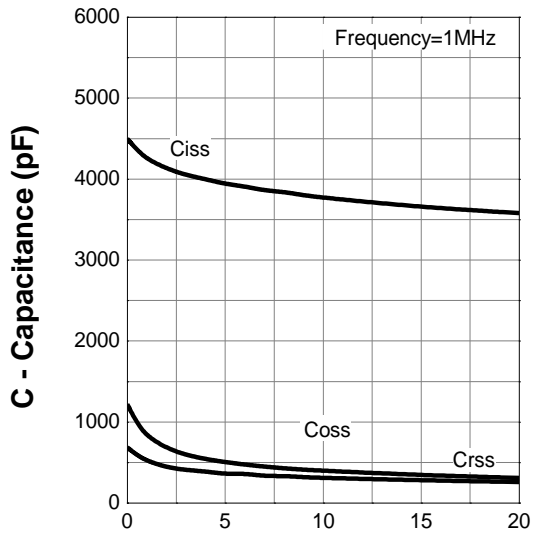
T_j - Junction Temperature ($^{\circ}\text{C}$)

Body Diode Characteristics



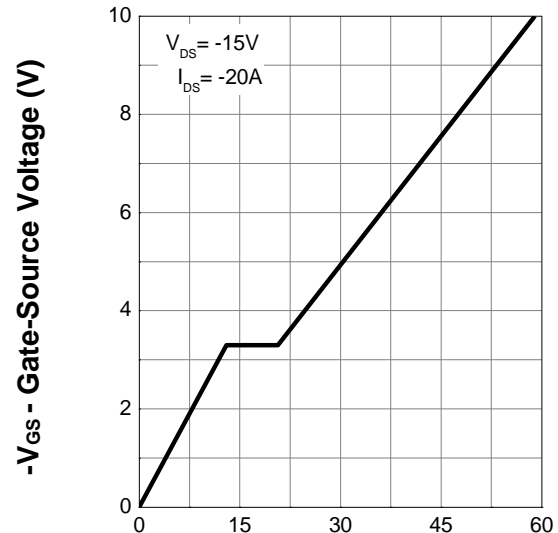
$-V_{SD}$ - Source-Drain Voltage (V)

Capacitance



$-V_{DS}$ - Drain-Source Voltage (V)

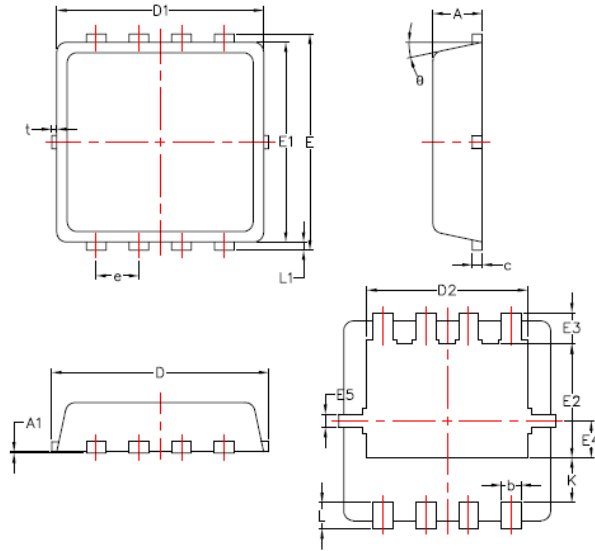
Gate Charge



Q_G - Gate Charge (nC)

8. Package Dimensions

PDFN3.3x3.3-8L Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	0.7	0.85
A1	/	0.05
b	0.20	0.40
c	0.10	0.25
D	3.15	3.45
D1	3.00	3.25
D2	2.29	2.65
E	3.15	3.45
E1	2.90	3.20
E2	1.54	1.94
E3	0.28	0.68
E4	0.37	0.77
E5	0.10	0.30
e	0.60	0.70
K	0.59	0.89
L	0.30	0.50
L1	0.06	0.20
T	0	0.13
θ	/	12°